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PATENT

DKT. NO.: 29273/502



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANTS : Hajime KAWANO, et al.
SERIAL NO. : 09/315,988
FILED : May 21, 1999
FOR : ELECTRON BEAM LITHOGRAPHY SYSTEM
GROUP ART : 2881
EXAMINER : Kalimah Fernandez

Assistant Commissioner for Patents
Washington D.C. 20231

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NOV 18 2002

TECHNOLOGY CENTER 2900

AMENDMENT

Sir:

In response to the office action dated May 22, 2002, the due date being extended by the attached Petition for Extension of Time, please amend the above-identified application as follows:

IN THE CLAIMS

Please amend claim 1 as follows:

1. (Amended) An electron beam lithograph system comprising:
exposure map creating means which, based on positional relations between meshes
dividing a region to be rendered by an electron beam on the one hand and shots to be rendered by
said electron beam on the other hand, creates an exposure map by calculating an area density
from a shot area included in each of said meshes; and
proximity effect correcting means for correcting a level of exposure for each of said shots
by referencing said exposure map so that each shot is exposed at the corrected level;
wherein said exposure map creating means includes judging means for judging whether
or not each shot straddles a plurality of meshes by using a plurality of memories and adding
circuits.